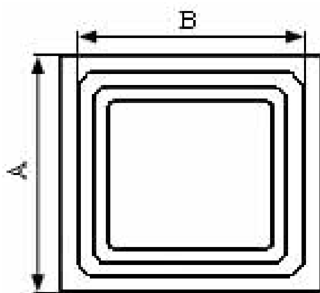
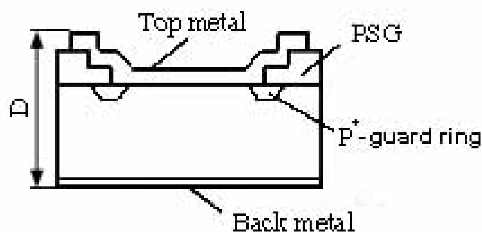
SCHOTTKY DIODES KDN-30020.
PRELIMINARY

Rev.1. Feb. 2010

VSP-MIKRON	30A/20V. Die Size-106*158mil.			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	20	25
Average Rectified Forward Current	$I_{F(AV)}$	A	30,0	-
DC Forward Voltage @ 25˚C, I_F=30,0A	V_F	V	0,50	0,48
Maximum Reverse Current @ 25˚C, V_R=25V 25˚C, V_R=20V 125˚C, V_R=20V	I_R	mA	- 0,600 400,0	0,600 0,550 350,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	300	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., T_J<150˚C.	I_{RRM}	A	5,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	˚C	150	





DIM	ITEM	µm
A_X A_y	Wafer Form Die Size	2700 4000
B_X B_y	Top Metal Size	2560 3860
D	Thickness	350max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;

b) ***Al-Ni-Ag***; - for Soldering.

*Backside metal: **Ti-Ni-Ag**.*

www.vsp-mikron.com